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**JP04358310**

**MAGNETO-RESISTANCE SENSOR**

**INTERNATL BUSINESS MACH CORP <IBM>**

**Inventor(s): DIENY BERNARD GURNEY BRUCE A ; LAMBERT STEVEN E ; MAURI DANIELE ;  
PARKIN STUART S P ; SPERIOSU VIRGIL S ; WILHOIT DENNIS R**

**Application No. 03337905, Filed 19911128, Published 19921211**

**Abstract: PURPOSE:** To provide a MR sensor which has linear sensitivity in a low magnetic field.

**CONSTITUTION:** The MR sensor has a 1st thin film layer 12 and a 2nd thin film layer 16 of a magnetic body which is partitioned with a thin film layer 14 of a nonmagnetic metal body. The 1st thin film layer is magnetically soft. When there is no magnetic field applied, the magnetism direction of the 1st thin film layer 12 is set orthogonal to the magnetism direction of the 2nd thin film layer 16 and the magnetism direction of the 2nd thin film layer 16 is fixed. A current is supplied to the MR sensor and variation in the voltage of the MR sensor based upon variation in the electric resistance of the MR sensor caused by the rotation of the magnetism of the 1st thin film layer 12 as a function of a magnetic field detected by the MR sensor is detected.

**Int'l Class:** G11B00539;

**Priority:** US 90 625343 19901211

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